

No.4646

**2SK1887**

N-Channel MOS Silicon FET

**SANYO**Very High-Speed  
Switching Applications**Features**

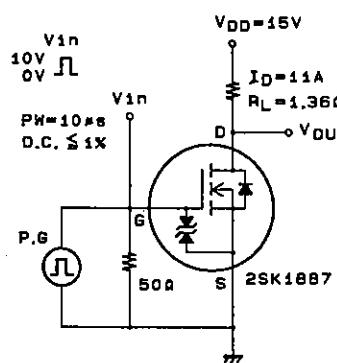
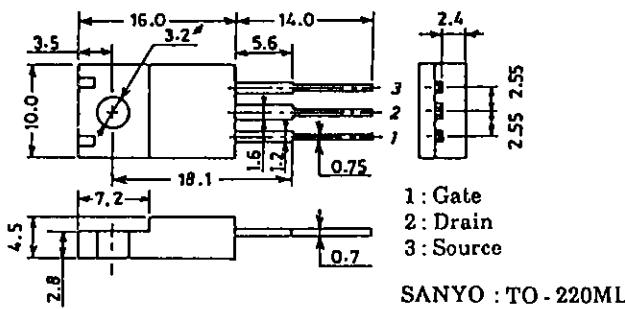
- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating easy mounting.

**Absolute Maximum Ratings at Ta = 25°C**

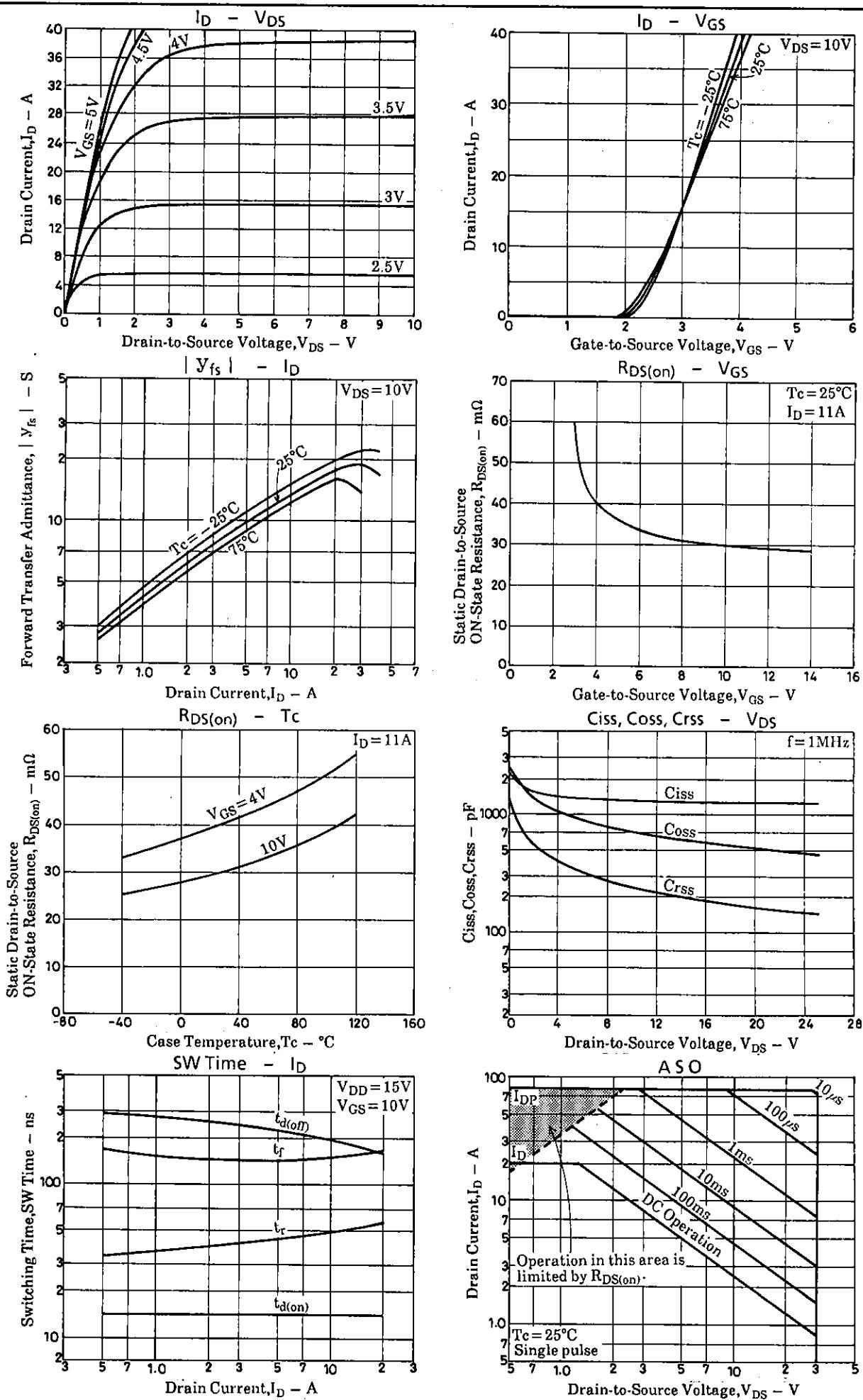
			unit
Drain-to-Source Voltage	V <sub>DSS</sub>	30	V
Gate-to-Source Voltage	V <sub>GSS</sub>	±20	V
Drain Current(DC)	I <sub>D</sub>	20	A
Drain Current(Pulse)	I <sub>DP</sub>	PW ≤ 10μs, duty cycle ≤ 1% 80	A
Allowable Power Dissipation	P <sub>D</sub>	2.0	W
		T <sub>c</sub> = 25°C 25	W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

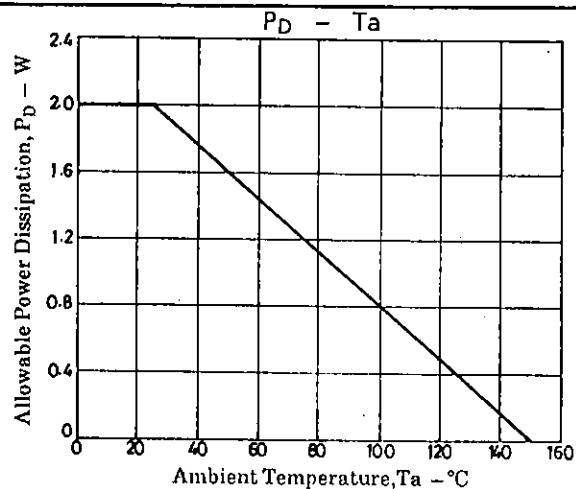
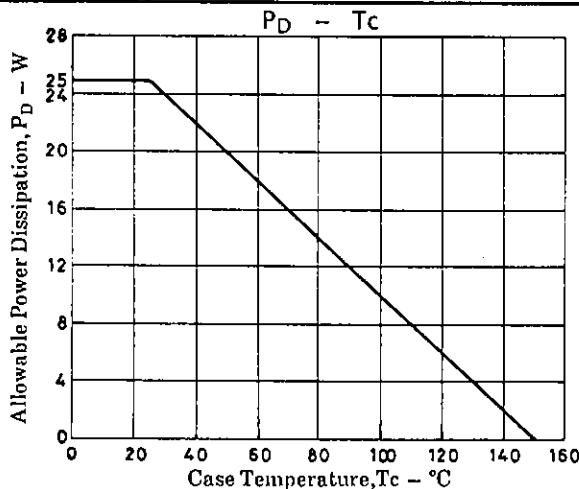
**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 1mA, V <sub>GS</sub> = 0	30			V
G-S Breakdown Voltage	V <sub>(BR)GSS</sub>	I <sub>G</sub> = ±100μA, V <sub>DS</sub> = 0	±20			V
Zero-Gate Voltage	I <sub>DSS</sub>	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0			100	μA
Drain Current						
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±16V, V <sub>DS</sub> = 0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA	1.0		2.0	V
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 11A	9	14.5		S
Static Drain-to-Source	R <sub>DS(on)</sub>	I <sub>D</sub> = 11A, V <sub>GS</sub> = 10V		30	40	mΩ
ON-State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> = 11A, V <sub>GS</sub> = 4V		40	55	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10V, f = 1MHz		1300		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 10V, f = 1MHz		720		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = 10V, f = 1MHz		240		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		14		ns
Rise Time	t <sub>r</sub>	"		50		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	"		290		ns
Fall Time	t <sub>f</sub>	"		150		ns
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 20A, V <sub>GS</sub> = 0		1.0	1.5	V

**Switching Time Test Circuit****Package Dimensions 2063A**  
(unit : mm)

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